

Silicon NPN Power Transistors

2SC5130

DESCRIPTION

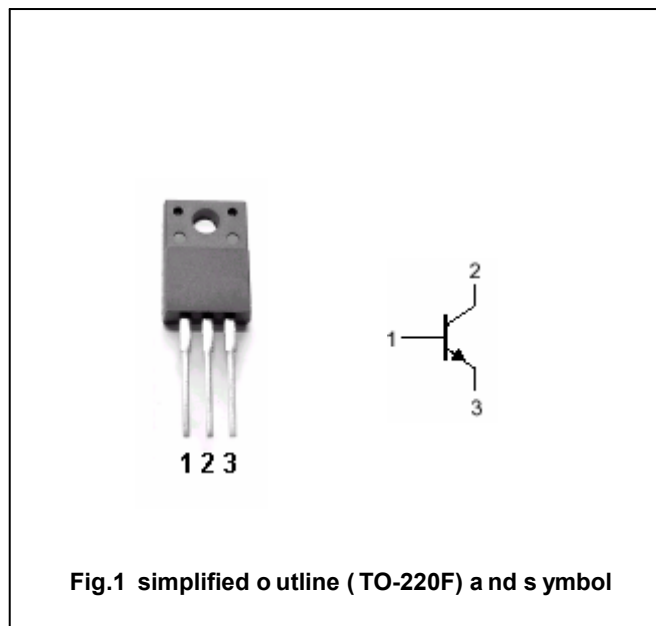
- With TO-220F package
- High voltage.
- High speed switching

APPLICATIONS

- For switching regulator and general purpose applications

PINNING

PIN DE	SCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL P	ARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	600	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	10	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		2	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg} S	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0			400	V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A ; I _B =0.3A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.5A ; I _B =0.3A			1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =500V ; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =10V ; I _C =0			10	μA
h _{FE}	DC current gain	I _C =1.5A ; V _{CE} =4V	10		30	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V ; f=1MHz		30		pF
f _T	Transition frequency	I _C =-0.3A ; V _{CE} =12V		20		MHz

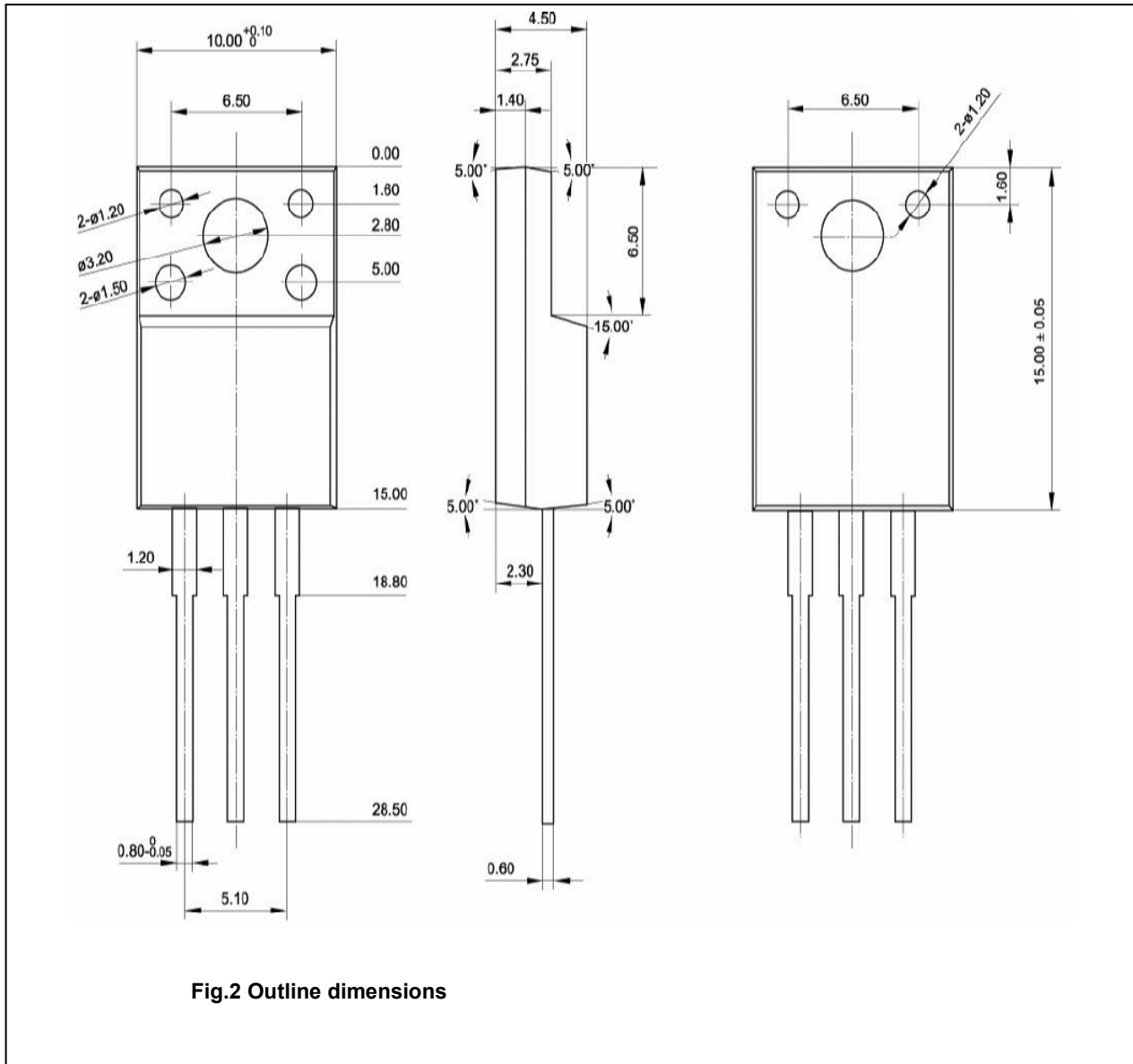
Switching times

t _{on}	Turn-on time	I _C =1.5A ; I _{B1} =0.15A I _{B2} =-0.3A V _{CC} =200V , R _L =133Ω			1.0	μs
t _s	Storage time				2.0	μs
t _f	Fall time				0.3	μs

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PACKAGE OUTLINE



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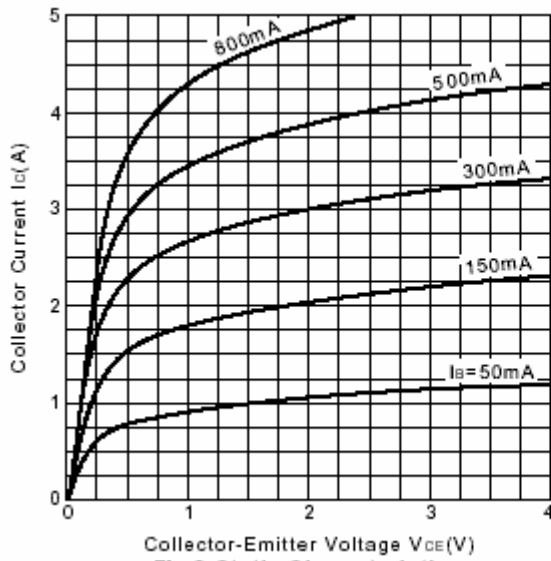


Fig.3 Static Characteristic

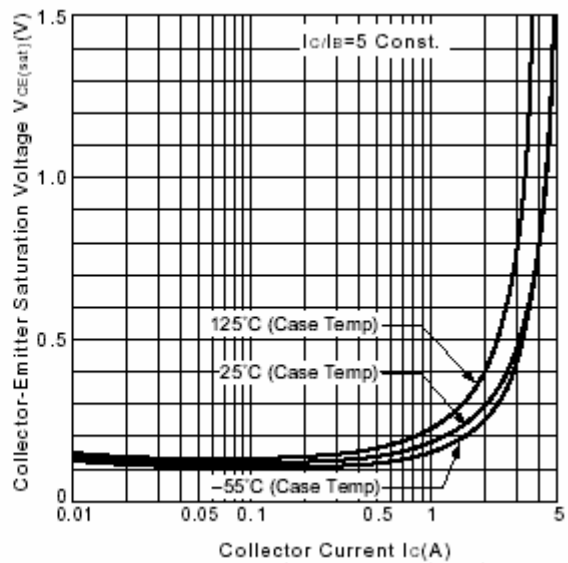


Fig.4 $V_{CE(sat)}$ - I_C Characteristics

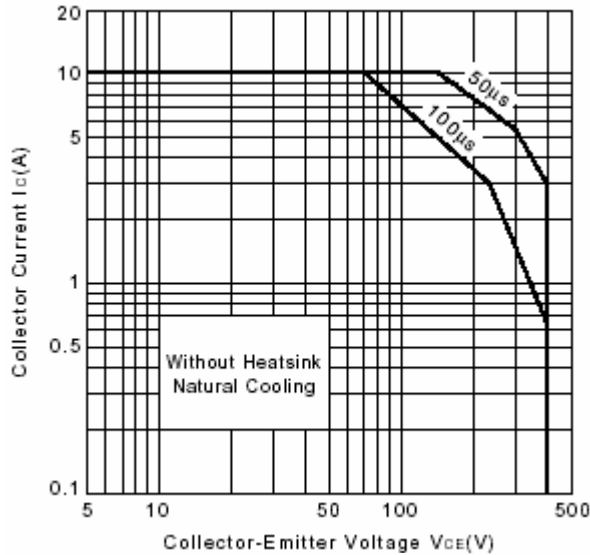


Fig.5 Safe Operating Area

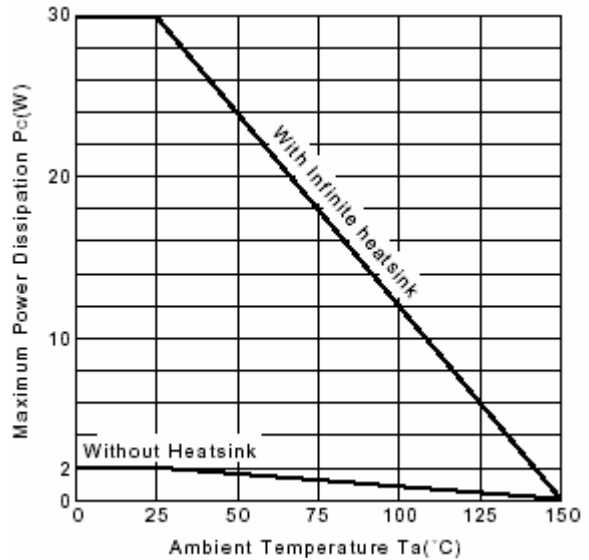


Fig.6 P_C - T_a Derating

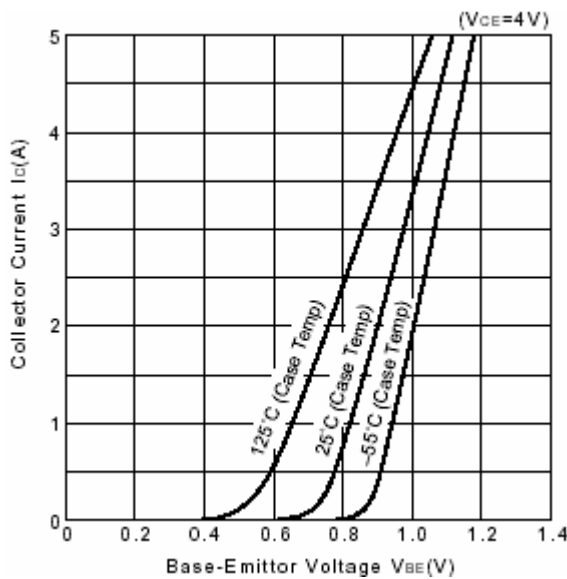


Fig.7 I_C - V_{BE}

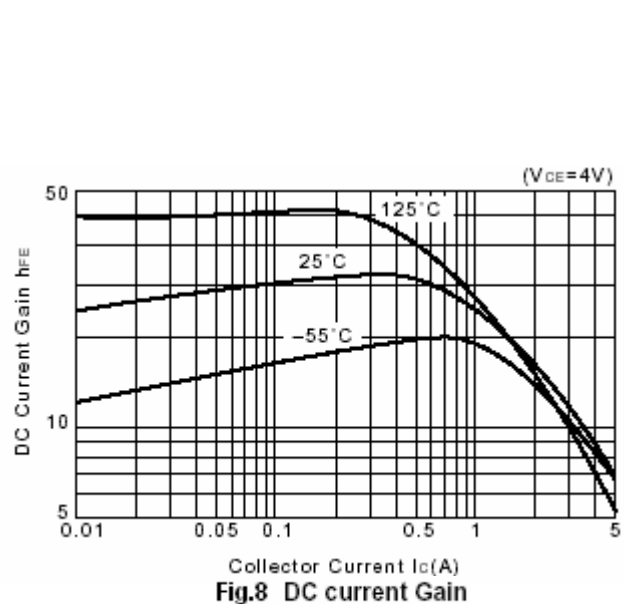


Fig.8 DC current Gain